

1-Line Bi-directional TVS Diode

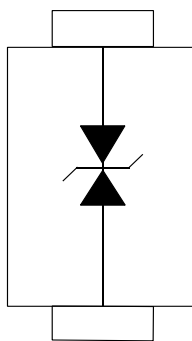
Description

The PESDU2481D1F is a bi-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power lines. The PESDU2481D1F complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a SOD-123FL lead-free package. The small size and high ESD/surge protection make PESDU2481D1F an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Operating voltage: 24V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 220A (8/20 μs)
- RoHS Compliant

Pin Configuration



Circuit and Pin Schematic

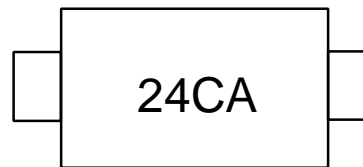
Mechanical Characteristics

- Package: SOD-123FL
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Marking Information: See Below

Applications

- Fast-charge battery chargers
- Power management system
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals

Marking Information



24CA = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU2481D1F	3000/Tape & Reel	7 inch

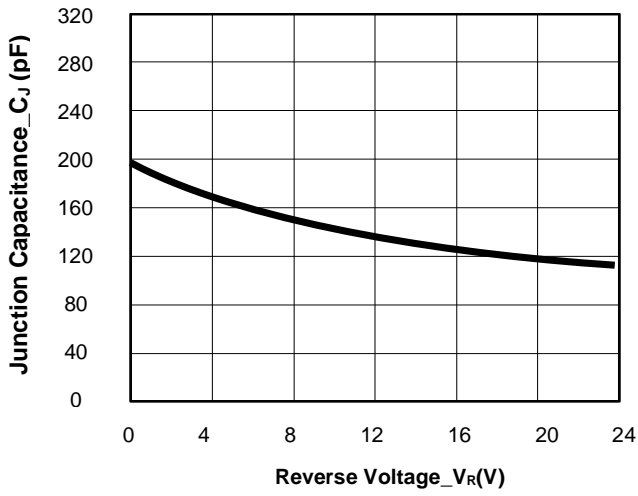
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{PK}	6600	W
Peak Pulse Current (8/20 μs)	I_{PP}	190	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 30 ± 30	kV
Operating Temperature Range	T_{OP}	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

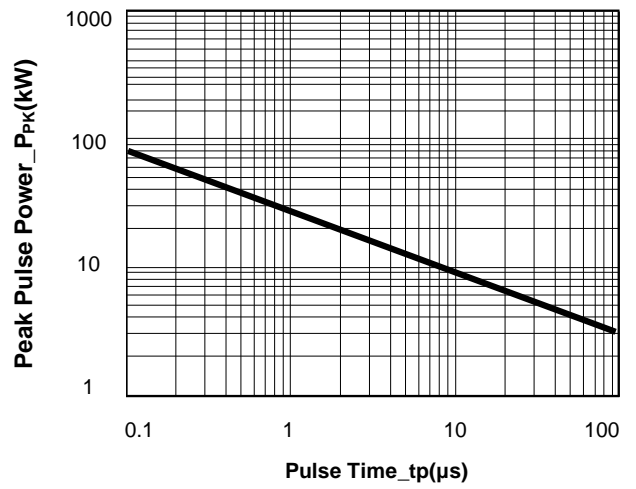
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			24	V	
Breakdown Voltage	V_{BR}	25			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			1.0	μA	$V_{RWM} = 24\text{V}$
Clamping Voltage	V_C		31	34	V	$I_{PP} = 150\text{A}$ (8/20 μs pulse)
Clamping Voltage	V_C		33	36	V	$I_{PP} = 190\text{A}$ (8/20 μs pulse)
Junction Capacitance	C_J		220		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

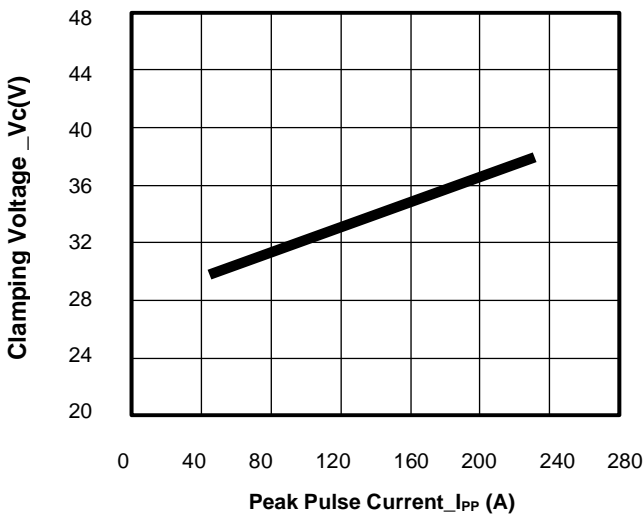
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



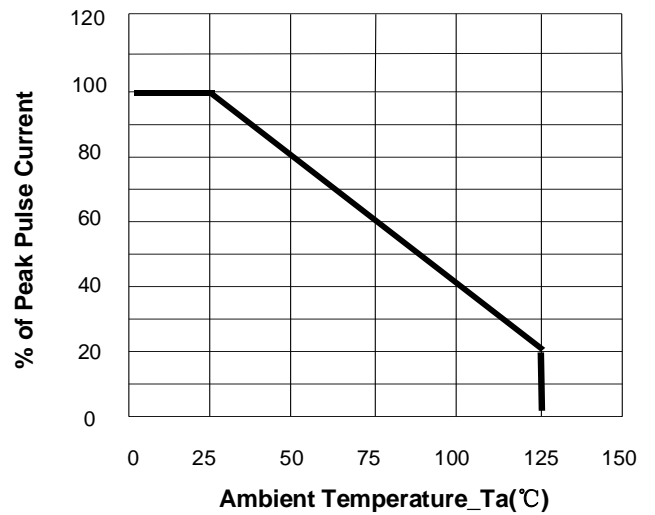
Junction Capacitance vs. Reverse Voltage



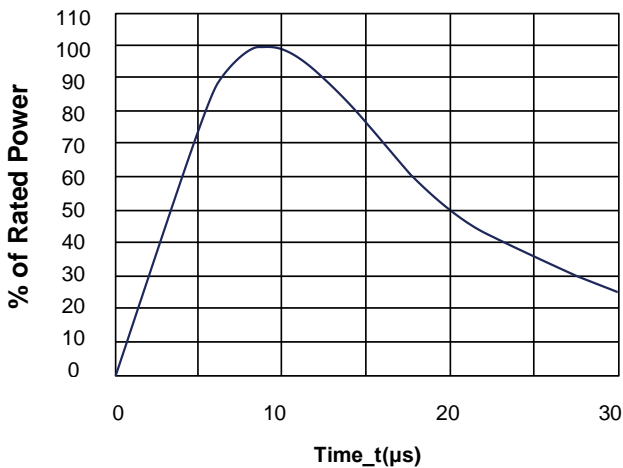
Peak Puls ePower vs. Pulse Time



Junction Capacitance vs. Reverse Voltage

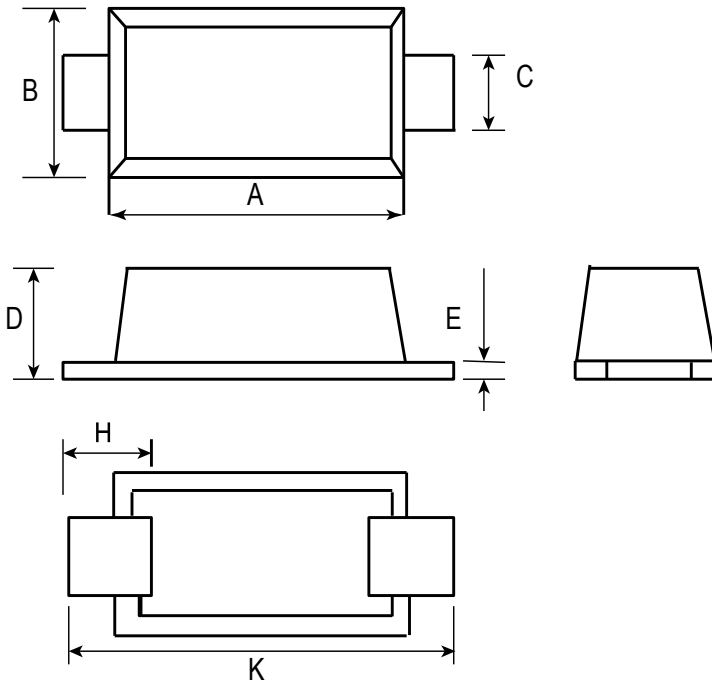


Power Derating Curve



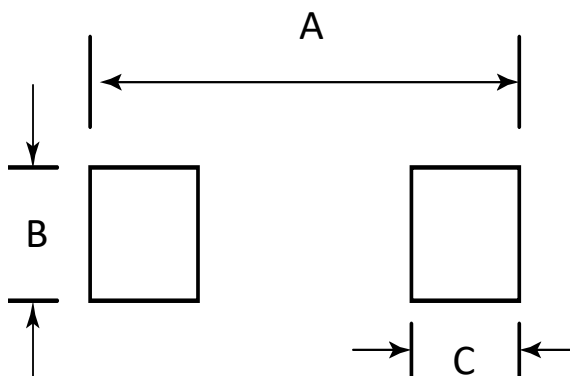
8/20 μs Pulse Waveform

SOD-123FL Package Outline Drawing



DIM	Millimeters		
	Min	Nom	Max
A	2.70	2.80	2.90
B	1.80	1.90	2.00
C	0.80	1.00	1.20
D			1.00
E	0.10	0.20	0.30
H	0.35		0.85
K	3.50		3.90

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	4.19	0.165
B	1.20	0.048
C	0.90	0.036

单击下面可查看定价，库存，交付和生命周期等信息

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